

FDP5680/FDB5680

60V N-Channel PowerTrench™ MOSFET

General Description

This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers.

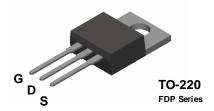
These MOSFETs feature faster switching and lower gate charge than other MOSFETs with comparable $R_{\scriptscriptstyle DS(\rm on)}$ specifications resulting in DC/DC power supply designs with higher overall efficiency.

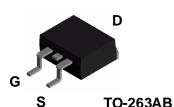
Features

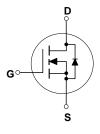
- 40 A, 60 V. R $_{\rm DS(ON)}$ = 0.020 Ω @ V $_{\rm GS}$ = 10 V $_{\rm DS(ON)}$ = 0.023 Ω @ V $_{\rm GS}$ = 6 V.
- Critical DC electrical parameters specified at evevated temperature.
- Rugged internal source-drain diode can eliminate the need for an external Zener diode transient suppressor.
- High performance trend technology for extremely low $\boldsymbol{R}_{\text{DS(ON)}}.$

FDB Series

• 175°C maximum junction temperature rating.







Absolute Maximum Ratings $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	FDP5680	FDB5680	Units
V _{DSS}	Drain-Source Voltage	6	V	
V _{GSS}	Gate-Source Voltage	±	20	V
I _D	Maximum Drain Current - Continuous	4	Α	
	- Pulsed	1		
P _D	Total Power Dissipation @ T _C = 25°C	6	W	
	Derate above 25°C	0.	W/°C	
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-65 to	+175	°C

Thermal Characteristics

R _e JC	Thermal Resistance, Junction-to-Case	2.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity
FDB5680	FDB5680	13"	24mm	800
FDP5680	FDP5680	Tube	N/A	45

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Drain-So	urce Avalanche Ratings (No	ote1)				
W _{DSS}	Single Pulse Drain-Source Avalanche Energy	$V_{DD} = 30 \text{ V}, I_D = 40 \text{A}$			90	mJ
I _{AR}	Maximum Drain-Source Avalanche	e Current			40	Α
Off Char	acteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	60			V
ABVoss ∧TJ	Breakdown Voltage Temperature Coefficient	$I_D = -250 \mu\text{A}$, Referenced to 25°C		60		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 48 V, V _{GS} = 0 V			1	μА
I _{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
On Chara	acteristics (Note 1)					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2	2.5	4	V
<u>A</u> VGS(th) ΔΤ _J	Gate Threshold Voltage Temperature Coefficient	I_D = -250 μ A, Referenced to 25°C		-6.4		mV/º(
R _{DS(on)}	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_D = 20 \text{ A},$ $V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}, T_J = 125 ^{\circ}\text{C}$ $V_{GS} = 6 \text{ V}, I_D = 19 \text{ A}$		0.016 0.022 0.018	0.020 0.035 0.023	Ω
I _{D(on)}	On-State Drain Current	$V_{GS} = 10 \text{ V}, V_{DS} = 5 \text{ V}$	20			Α
g _{FS}	Forward Transconductance	$V_{DS} = 5 \text{ V}, I_{D} = 20 \text{ A}$		43		S
Dynamic	Characteristics					
C _{iss}	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$		1850		pF
C _{oss}	Output Capacitance	f = 1.0 MHz		230		pF
C _{rss}	Reverse Transfer Capacitance			95		pF
Switchin	g Characteristics (Note 1)					
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 30 \text{ V}, I_D = 1 \text{ A},$		15	27	ns
t _r	Turn-On Rise Time	$V_{GS} = 10 \text{ V}, R_{GEN} = 6 \Omega$		9	18	ns
t _{d(off)}	Turn-Off Delay Time			35	56	ns
t _f	Turn-Off Fall Time			16	26	ns
Q _g	Total Gate Charge	V _{DS} = 30 V, I _D = 20 A		33	46	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 10 V		6.5		nC
Q_{gd}	Gate-Drain Charge			7.5		nC
Drain-So	urce Diode Characteristics	and Maximum Ratings				
<u>טומווו-30</u> _s	Maximum Continuous Drain-Source				40	Α
V _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_S = 20 \text{ A}$ (Note 1)		0.9	1.2	V

^{1.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

Typical Characteristics

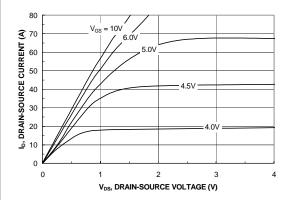


Figure 1. On-Region Characteristics.

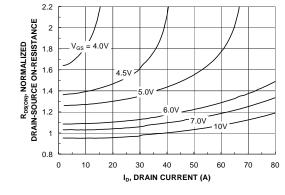


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

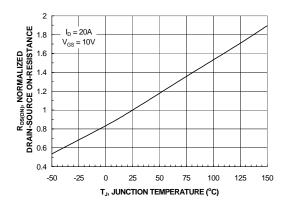


Figure 3. On-Resistance Variation with Temperature.

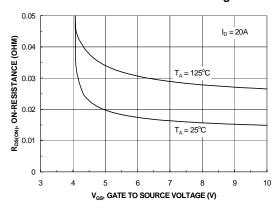


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

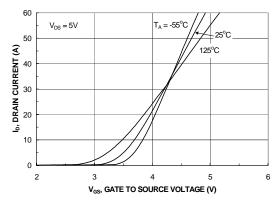


Figure 5. Transfer Characteristics.

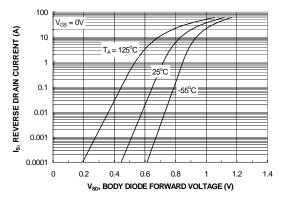
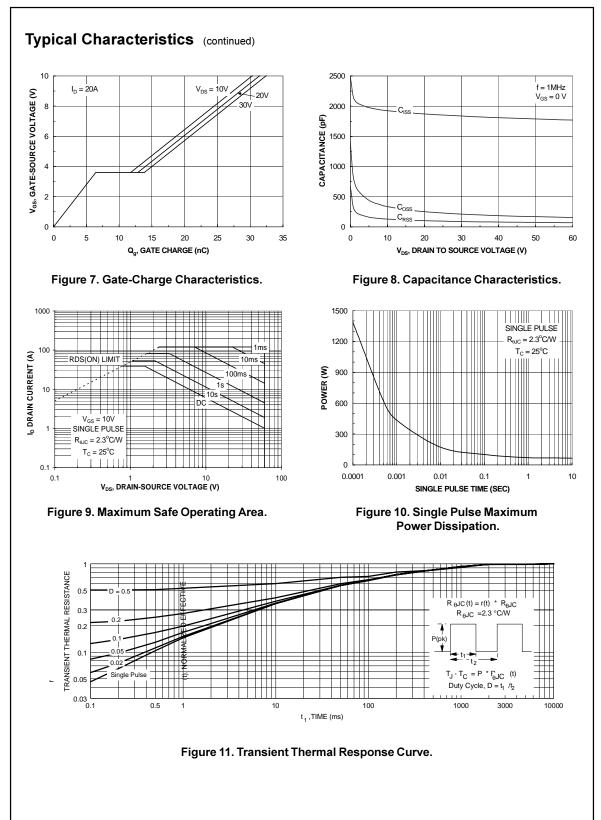
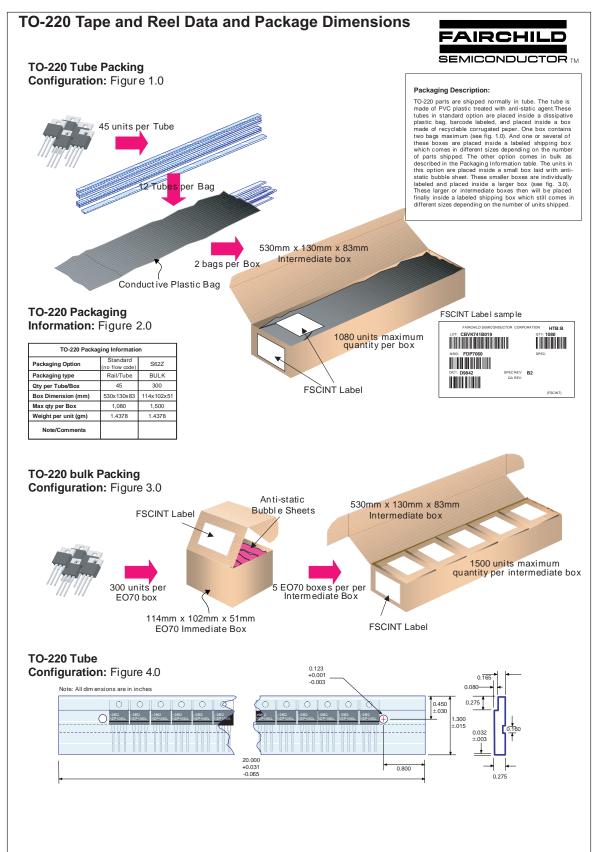


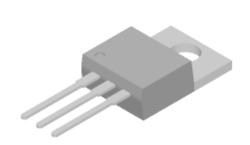
Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

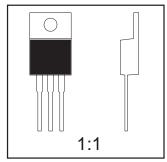




TO-220 Tape and Reel Data and Package Dimensions, continued

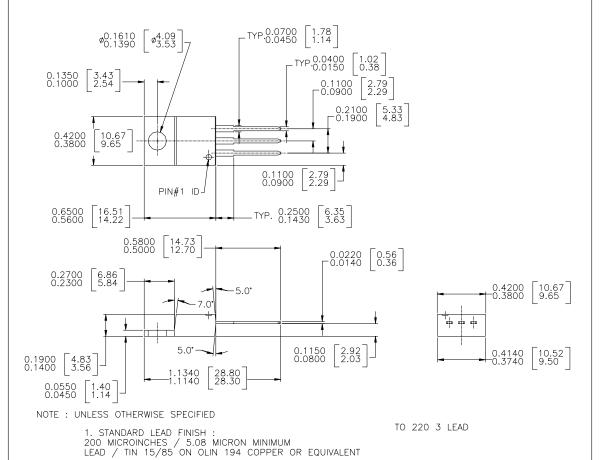
TO-220 (FS PKG Code 37)



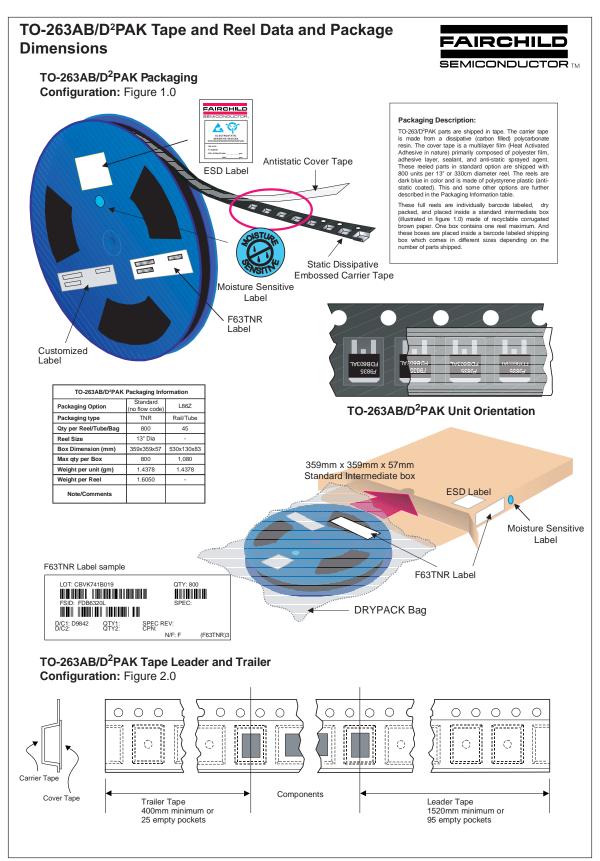


Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

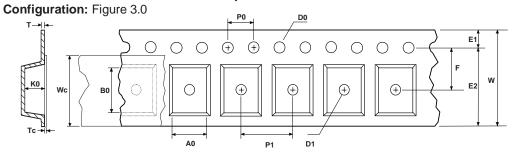
Part Weight per unit (gram): 1.4378



2. DIMENSION BASED ON JEDEC STANDARD TO-220 VARIATION AB, ISSUE J, DATED 3/24/87



TO-263AB/D²PAK Embossed Carrier Tape





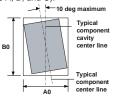
	Dimensions are in millimeter													
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	Т	Wc	Тс
TO263AB/ D ² PAK (24mm)	10.60 +/-0.10	15.80 +/-0.10	24.0 +/-0.3	1.55 +/-0.05	1.60 +/-0.10	1.75 +/-0.10	22.25 min	11.50 +/-0.10	16.0 +/-0.1	4.0 +/-0.1	4.90 +/-0.10	0.450 +/-0.150	21.0 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)

Component Rotation



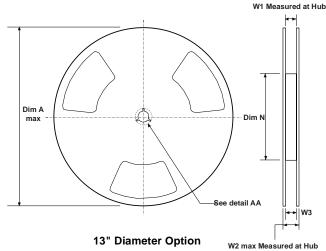
Sketch B (Top View)
Component Rotation

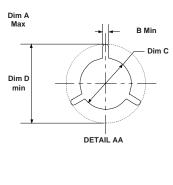


Sketch C (Top View)

Component lateral movement

TO-263AB/D²PAK Reel Configuration: Figure 4.0

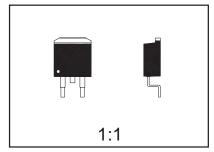




	Dimensions are in inches and millimeters								
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
24mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.961 +0.078/-0.000 24.4 +2/0	1.197 30.4	0.941 - 0.1.079 23.9 - 27.4

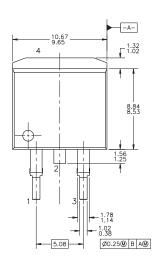
TO-263AB/D²PAK (FS PKG Code 45)

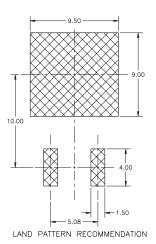


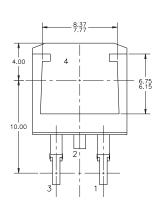


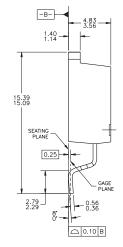
Scale 1:1 on letter size paper Dimensions shown below are in: inches [millimeters]

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 EQUIVALENT.
 C) MAXIMUM VERTICAL BURR ON HEATSINK NOT
 TO EXCEED 0.003 INCH / 0.05mm.
 D) NO PACKAGE CHIPS, CRACKS OR SURFACE
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 E) REFERENCE JEDEC, TO-263, ISSUE C,
 VARIATION AB, DATED 2/92.

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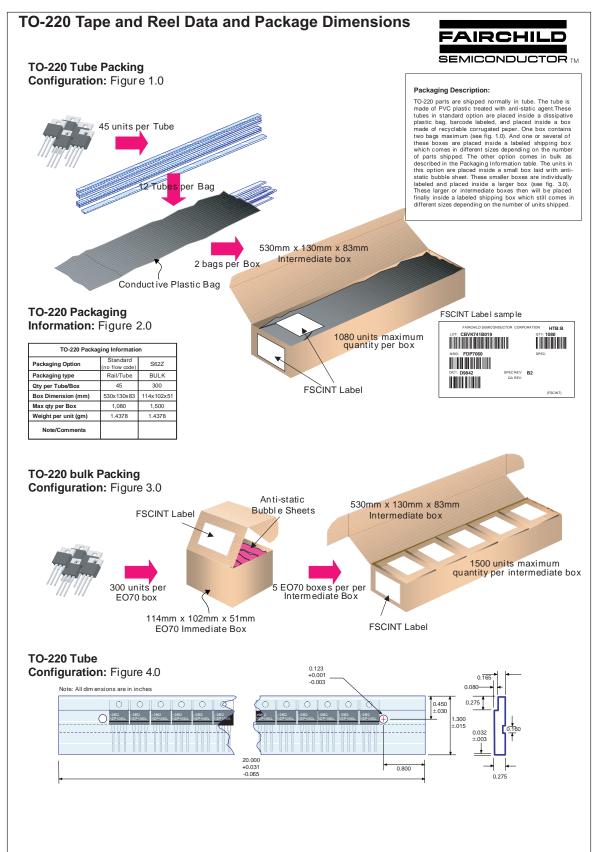
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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

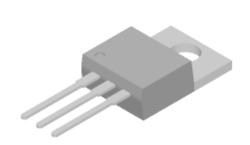
Definition of Terms

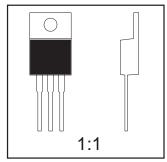
Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.



TO-220 Tape and Reel Data and Package Dimensions, continued

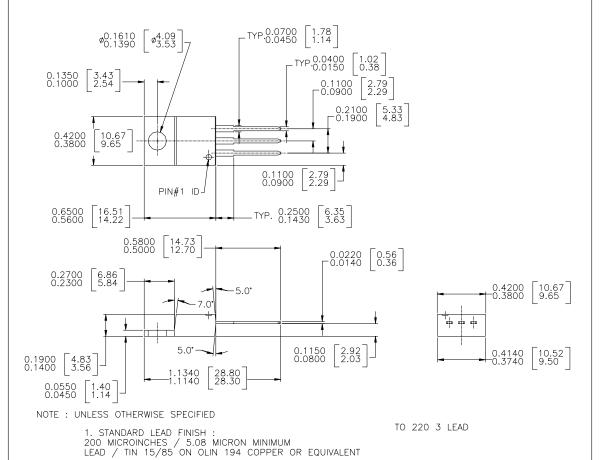
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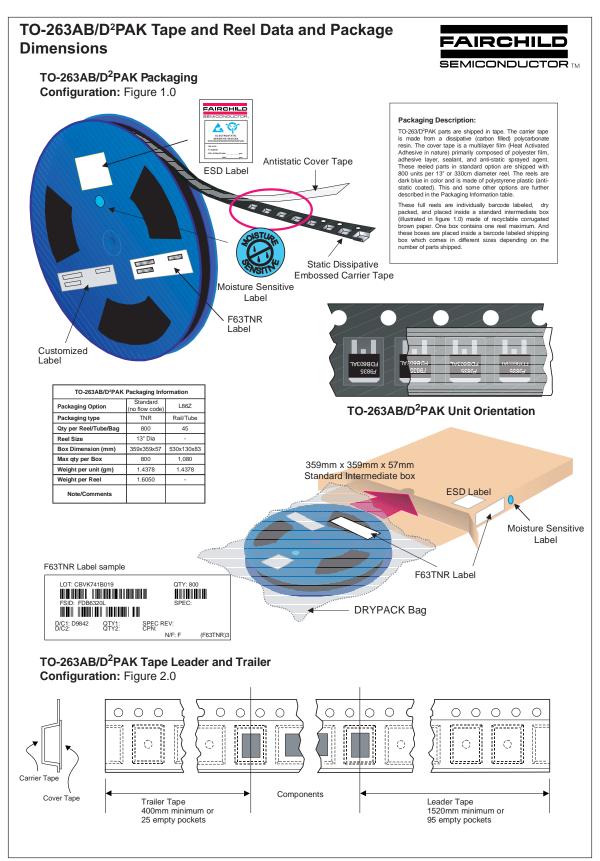


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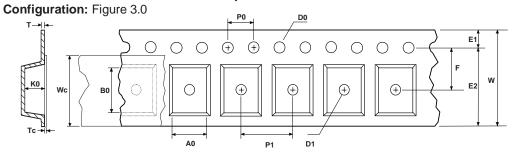
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TO-263AB/D²PAK Embossed Carrier Tape





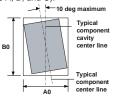
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Sketch A (Side or Front Sectional View)

Component Rotation



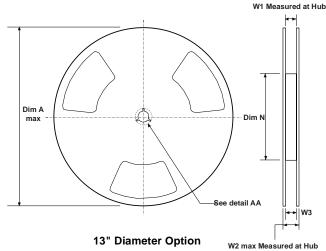
Sketch B (Top View)
Component Rotation

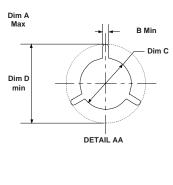


Sketch C (Top View)

Component lateral movement

TO-263AB/D²PAK Reel Configuration: Figure 4.0

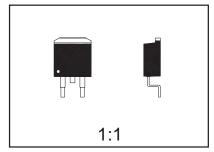




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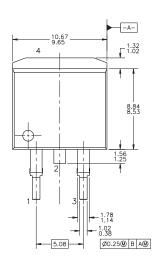
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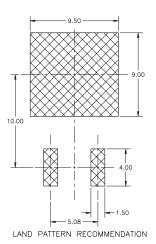


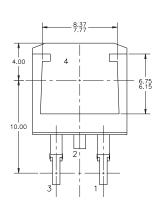


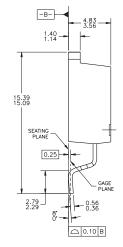
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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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